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ORM PTO-1449 US Dept. of Commerce			ATTORNEY DOCKET NO.		SERIAL NO.						
Patent and rademark Office				ATML 515	10/015,326						
				ATMI-515 10/015,326 APPLICANT							
INFORMATION DISCLOSURE STATEMENT				Chongying Xu, et al.							
(use several sheets if necessary)				FILING DATE		GROUP					
				December 13, 2001		TBA					
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